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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No. 10/041,896
 Filing Date January 7, 2002
 Inventor Brenda D. Kraus et al
 Assignee Micron Technology, Inc.
 Group Art Unit 2813
 Examiner Yennhu B. Huynh
 Attorney Docket No. MI22-1859
 Title: DRAM Circuitry Having Storage Capacitors Which Include Capacitor
 Dielectric Regions Comprising Aluminum Nitride

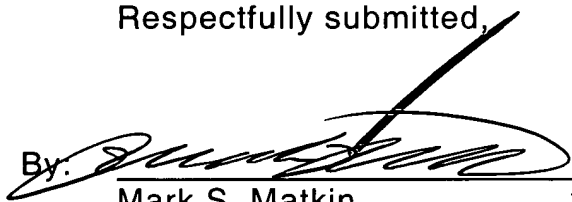
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with
 37 CFR §1.56. Copies of the cited art are included. No admission is made
 regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: 5-29-03

By: 
 Mark S. Matkin
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